



FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. ASMEX.284C1	APPLICATION NO. 10/826,212
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		APPLICANT Pomarede, et al.	
(USE SEVERAL SHEETS IF NECESSARY)		FILING DATE July 24, 2003	GROUP Unknown 2823

U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
<i>Lee</i>	1	2,394,930	2/12/46	McRae			
	2	3,895,127	7/15/75	Comizzoli			
	3	4,056,642	11/1/77	Saxena et al.			
	4	4,292,343	9/29/81	Plaettner et al.			
	5	4,343,830	8/10/82	Sarma et al.			
	6	4,436,761	3/13/84	Hayashi et al.			
	7	4,544,571	10/1/85	Miller			
	8	4,645,683	2/24/87	Gourrier et al.			
	9	4,766,006	8/23/88	Gaczi			
	10	5,135,775	8/4/92	Foller et al.			
	11	5,281,546	01/25/94	Possin et al.			
	12	5,576,071	11/19/96	Sandhu			
	13	5,587,205	12/24/96	Saito et al.			
	14	5,780,115	7/14/98	Park et al.			
	15	5,939,763	08/17/99	Hao et al.			
	16	5,950,107	09/07/99	Huff et al.			
	17	5,990,013	11/23/99	Berenguer et al.			
	18	5,993,916	11/30/99	Zhao et al.			
<i>Lee</i>	19	6,107,192	08/22/00	Subrahmanyam et al.			
<i>Lee</i>	20	6,200,866	03/13/01	Ma et al.			

FOREIGN PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
					YES	NO	
<i>Lee</i>	21	JP 60 254621 A	16.12.85	Patent Abstracts of Japan			
<i>Lee</i>	22	JP 2000 160342 A	13.10.00	Patent Abstracts of Japan			
<i>Lee</i>	23	0 617 461. A2	03/16/94	EPO			

EXAMINER	<i>Tran My Lee</i>	DATE CONSIDERED	<i>5/27/2004</i>
*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.			

0  
OCT 10 2003  
SEP 22 2003  
PATENT & TRADEMARK OFFICE

SHEET 2 OF 2

FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. ASMEC.284C1	APPLICATION NO. 10/626,212
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		APPLICANT Pomarede, et al.	
(USE SEVERAL SHEETS IF NECESSARY)		FILING DATE July 24, 2003	GROUP Unknown 2823

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
<i>Lee</i>	24 Kim, H. and R. Reif, <i>Thin Solid Films</i> , Vol. 289:192-198 (1996), "In-situ low-temperature (600°C) wafer surface cleaning by electron cyclotron resonance hydrogen plasma ...."
<i>Lee</i>	25 Ramm J. and E. Beck, <i>Thin Solid Films</i> , Vol. 246:158-163 (1994), "Low temperature epitaxial growth by molecular beam epitaxy on hydrogen-plasma-cleaned silicon wafers."

H:\DOCS\KFS\KFS-2698.DOC  
091803

EXAMINER	<i>Klaus M. Lee</i>	DATE CONSIDERED	<i>5/27/2004</i>
*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.			